

SEMICONDUCTOR DEVICE AND METHOD FOR MANUFACTURING THE SAME

ABSTRACT

A semiconductor device and a method for manufacturing the same are provided. The semiconductor device includes a well region, a drain region and a source region disposed in the well region, a gate electrode disposed above the well region, a thin gate insulating layer and a thick gate insulating layer disposed under the gate electrode, the thick gate insulating layer being disclosed closer to the drain region than the thin gate insulating layer, and an extended drain junction region disposed below the gate electrode.

(Figure 1)

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